Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-124-0289

Inclosure Material:	
Glass and metal	
Overall Length:	
Between 0.293 inch	es and 0.357 inches
Terminal Length:	
Between 1.000 inch	es and 1.625 inches
Overall Diameter:	
Between 0.215 inch	es and 0.235 inches
Function For Whic	h Designed:
Transient suppresso	n
End Application:	
Tacamo tip e/i fscm	13499
Joint Electronic De	evice Engineering Council/jedec/case Outline Designation:
Do-13	
Electrode Internall	y-electrically Connected To Case:
Cathode	
Mounting Method:	
Terminal	
Features Provided	:
Hermetically sealed	case
Semiconductor Ma	iterial:
Silicon	
Voltage Rating In V	/olts Per Characteristic:
7.9 breakdown volt	age, dc
Current Rating Per	Characteristic:
10.00 milliamperes	forward current, average peak
Power Rating Per	Characteristic:
1.0 watts small-sign	al input power, common-collector major
Maximum Operatir	ng Tempurature Per Measurement Point:
175.0 degrees celsi	us ambient air
Test Data Docume	nt:
81349-mil-s-19500	specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes co	mmercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and p	performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And	I Quantity:
2 uninsulated wire lo	ead
Specification Data	:
81349-mil-s-19500/	500 government specification
Shelf Life:	
N/a	
Unit Of Measure:	
 Domilitori-stisse	
Demilitarization: No	

## NSN 5961-01-124-0289

Diode Semiconductor Device - Page 2 of 2

**Fiig:** A110a0

